

January 2001 Revised August 2001

74LVT32244 • 74LVTH32244 Low Voltage 32-Bit Buffer/Line Driver with 3-STATE Outputs (Preliminary)

General Description

The LVT32244 and LVTH32244 contain thirty-two non-inverting buffers with 3-STATE outputs designed to be employed as a memory and address driver, clock driver, or bus oriented transmitter/receiver. The device is nibble controlled. Individual 3-STATE control inputs can be shorted together for 8-bit, 16-bit, or 32-bit operation.

The LVTH32244 data inputs include bushold, eliminating the need for external pull-up resistors to hold unused inputs.

These buffers and line drivers are designed for low-voltage (3.3V) V_{CC} applications, but with the capability to provide a TTL interface to a 5V environment. The LVT32244 and LVTH32244 are fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining a low power dissipation

Features

- Input and output interface capability to systems at 5V V_{CC}
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs (74LVTH32244), also available without bushold feature (74LVT32244).
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading
- Outputs source/sink -32 mA/+64 mA
- ESD performance:

Human-body model > 2000V

Machine model > 200V

Charged-device model > 1000V

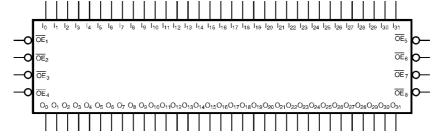
 Packaged in plastic Fine-Pitch Ball Grid Array (FBGA) (Preliminary)

Ordering Code:

Order Number	Package Number	Package Description
74LVT32244GX (Note 1)	BGA96A (Preliminary)	96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide [Tape and Reel]
74LVTH32244GX (Note 1)		96-Ball Fine-Pitch Ball Grid Array (FBGA), JEDEC MO-205, 5.5mm Wide [Tape and Reel]

Note 1: BGA package available in Tape and Reel only.

Logic Symbol



Connection Diagram

1 2 3 4 5 6 000000 000000 O 00000 000000 000000 000000

(Top Thru View)

Pin Descriptions

Pin Names	Description	
OE _n	Output Enable Input (Active LOW)	
I ₀ -I ₃₁	Inputs	
O ₀ -O ₃₁	Outputs	

Pin Assignments for FBGA

	1	2	3	4	5	6
Α	01	O ₀	OE ₁	OE ₂	I ₀	I ₁
В	O ₃	02	GND	GND	l ₂	l ₃
С	O ₅	04	V _{CC1}	V _{CC1}	I ₄	I ₅
D	O ₇	O ₆	GND	GND	I ₆	I ₇
E	O ₉	O ₈	GND	GND	I ₈	l ₉
F	O ₁₁	O ₁₀	V _{CC1}	V _{CC1}	I ₁₀	I ₁₁
G	O ₁₃	O ₁₂	GND	GND	I ₁₂	I ₁₃
Н	O ₁₄	O ₁₅	ŌE ₄	ŌE ₃	I ₁₅	I ₁₄
J	O ₁₇	O ₁₆	OE ₅	OE ₆	I ₁₆	I ₁₇
K	O ₁₉	O ₁₈	GND	GND	I ₁₈	I ₁₉
L	O ₂₁	O ₂₀	V_{CC2}	V_{CC2}	I ₂₀	l ₂₁
M	O ₂₃	O ₂₂	GND	GND	l ₂₂	l ₂₃
N	O ₂₅	O ₂₄	GND	GND	l ₂₄	l ₂₅
Р	O ₂₇	O ₂₆	V_{CC2}	V_{CC2}	I ₂₆	l ₂₇
R	O ₂₉	O ₂₈	GND	GND	l ₂₈	l ₂₉
Т	O ₃₀	O ₃₁	OE ₈	OE ₇	l ₃₁	I ₃₀

Truth Tables

Inp	uts	Outputs
OE ₁	l ₀ -l ₃	O ₀ -O ₃
L	L	L
L	Н	Н
Н	Χ	Z

Inp	uts	Outputs
OE ₂	l ₄ -l ₇	O ₄ -O ₇
L	L	L
L	Н	Н
Н	Χ	Z

Inp	outs	Outputs
ŌE ₃	I ₈ -I ₁₁	O ₈ -O ₁₁
L	L	L
L	H.S.	Н
Н	x /h	Z

Inp	uts	Outputs
ŌE ₄	l ₁₂ -l ₁₅	O ₁₂ -O ₁₅
L		L
- L O	Н	Н
H	Χ	Z

Inp	outs	Outputs
OE ₅	I ₁₆ -I ₁₉	O ₁₆ -O ₁₉
L	L	L
L	Н	Н
Н	Χ	Z

Inp	outs	Outputs
OE ₆	l ₂₀ -l ₂₃	O ₂₀ -O ₂₃
L	L	L
L	Н	Н
Н	X	Z

Inp	outs	Outputs
OE ₇	l ₂₄ -l ₂₇	O ₂₄ -O ₂₇
L	L	L
L	Н	Н
Н	Χ	Z

Inp	outs	Outputs
OE ₈	l ₂₈ -l ₃₁	O ₂₈ -O ₃₁
L	L	L
L	Н	Н
Н	X	Z

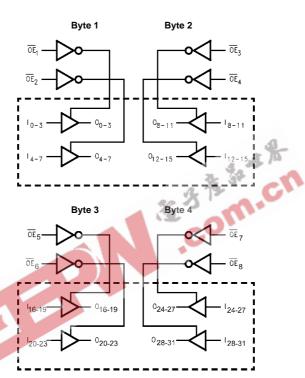
H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial (HIGH or LOW, inputs may not float)
Z = High Impedance

Functional Description

The 74LVT32244 and 74LVTH32244 contain thirty-two non-inverting buffers with 3-STATE outputs. The device is nibble (4 bits) controlled with each nibble functioning identically, but independent of the other. The control pins can be shorted together to obtain full 32-bit operation. The

3-STATE outputs are controlled by an Output Enable (\overline{OE}_n) input. When \overline{OE}_n is LOW, the outputs are in the 2-state mode. When \overline{OE}_n is HIGH, the standard outputs are in the high impedance mode but this does not interfere with entering new data into the inputs.

Logic Diagrams



 V_{CC1} is associated with Bytes 1 and 2.

V_{CC2} is associated with Bytes 3 and 4.

Note: Please note that these diagrams are provided only for the understanding of logic operations and should not be used to estimate propagation delays.

Symbol	Parameter	Value	Conditions	Units
V _{CC}	Supply Voltage	-0.5 to +4.6		V
/ _I	DC Input Voltage	-0.5 to +7.0		V
/ ₀	Output Voltage	-0.5 to +7.0	Output in 3-STATE	V
		-0.5 to +7.0	Output in High or Low State (Note 3)	_ v
IK	DC Input Diode Current	-50	V _I < GND	mA
ОК	DC Output Diode Current	-50	V _O < GND	mA
0	DC Output Current	64	V _O > V _{CC} Output at HIGH State	mA
		128	V _O > V _{CC} Output at LOW State	
СС	DC Supply Current per Supply Pin	±64		mA
GND	DC Ground Current per Ground Pin	±128		mA
$\Gamma_{\rm STG}$	Storage Temperature	-65 to +150		°C

Recommended Operating Conditions

Symbol	Parameter	Min 🦽	Max	Units
V _{CC}	Supply Voltage	2.7	3.6	V
VI	Input Voltage	0	5.5	V
I _{OH}	High-Level Output Current	4	-32	mA
I _{OL}	Low-Level Output Current	-0.1	64	mA
T _A	Free Air Operating Temperature	-40	+85	°C
Δt/ΔV	Input Edge Rate, V _{IN} = 0.8V-2.0V, V _{CC} = 3.0V	0	10	ns/V

Note 2: Absolute Maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum rated conditions is not implied.

Note 3: Io Absolute Maximum Rating must be observed.

DC Electrical Characteristics

Symbol	Parameter Parameter		V _{CC}	V_{CC} $T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		Units	Conditions	
Зуппоот			(V)	Min Max		Units		
V _{IK}	Input Clamp Diode Vo	ltage	2.7		-1.2	V	$I_1 = -18 \text{ mA}$	
V _{IH}	Input HIGH Voltage		2.7-3.6	2.0		V	$V_0 \le 0.1V$ or	
V _{IL}	Input LOW Voltage		2.7-3.6		0.8	V	$V_O \ge V_{CC} - 0.1V$	
V _{OH}	Output HIGH Voltage		2.7–3.6	V _{CC} – 0.2			$I_{OH} = -100 \mu A$	
			2.7	2.4		V	$I_{OH} = -8 \text{ mA}$	
				2.0			$I_{OH} = -32 \text{ mA}$	
V _{OL}	Output LOW Voltage	Output LOW Voltage			0.2		I _{OL} = 100 μA	
					0.5		I _{OL} = 24 mA	
					0.4	V	I _{OL} = 16 mA	
			3.0		0.5		I _{OL} = 32 mA	
			3.0		0.55		I _{OL} = 64 mA	
I _{I(HOLD)}	Bushold Input Minimu	m Drive	3.0	75		μА	$V_1 = 0.8V$	
(Note 4)				-75		μΑ	$V_1 = 2.0V$	
I _{I(OD)}	Bushold Input Over-Drive		3.0	500		μА	(Note 5)	
(Note 4)	Current to Change St	Current to Change State		-500] ""	(Note 6)	
I _I	Input Current		3.6		10		V _I = 5.5V	
		Control Pins	3.6		±1	μА	$V_I = 0V \text{ or } V_{CC}$	
		Data Pins	3.6		− 5	μ	$V_I = 0V$	
		Data i ilis	3.0		1		$V_I = V_{CC}$	
l _{OFF}	Power Off Leakage C	urrent	0		±100	μΑ	$0V \le V_I \text{ or } V_O \le 5.5V$	
I _{PU/PD}	Power Up/Down		0 – 1.5V		±100	μА	$V_0 = 0.5V \text{ to } 3.0V$	
	3-STATE Current	3-STATE Current			±100	μΛ	$V_I = GND \text{ or } V_{CC}$	
I _{OZL}	3-STATE Output Leakage Current		3.6		- 5	μΑ	V _O = 0.5V	
I _{OZH}	3-STATE Output Leak	age Current	3.6		5	μΑ	V _O = 3.0V	
I _{OZH} +	3-STATE Output Leakage Current		3.6		10	μΑ	$V_{CC} < V_O \le 5.5V$	

DC Electrical Characteristics (Continued)

Symbol	Parameter		V_{CC} $T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		Units	Conditions	
Oyillboi	i arameter	(V) Min Max		Oilles	Conditions		
I _{CCH}	Power Supply Current	V _{CC1} or V _{CC2}	3.6		0.19	mA	Outputs High
I _{CCL}	Power Supply Current	V _{CC1} or V _{CC2}	3.6		5.0	mA	Outputs Low
I _{CCZ}	Power Supply Current	V _{CC1} or V _{CC2}	3.6		0.19	mA	Outputs Disabled
I _{CCZ} +	Power Supply Current	V _{CC1} or V _{CC2}	3.6		0.19	mA	$V_{CC} \le V_O \le 5.5V$, Outputs Disabled
ΔI_{CC}	Increase in Power Supply Current		3.6		0.2	mA	One Input at V _{CC} – 0.6V
	(Note 7)	V _{CC1} or V _{CC2}					Other Inputs at V _{CC} or GND

Note 4: Applies to bushold versions only (LVTH32244).

Note 5: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 6: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

 $\textbf{Note 7:} \ This is the increase in supply current for each input that is at the specified voltage level rather than V_{CC} or GND.$

Dynamic Switching Characteristics (Note 8)

Symbol	Parameter	v _{cc}	T _A = 25°C			Units	Conditions	
Symbol	Faiametei	(V)	Min Typ Max		Max	A /	$\textbf{C}_{\textbf{L}} = \textbf{50}~\text{pF,}~\textbf{R}_{\textbf{L}} = \textbf{500}\Omega$	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	3.3		8.0	n. 73	V	(Note 9)	
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	3.3		-0.8	Agr. d.	V	(Note 9)	

Note 8: Characterized in SSOP package. Guaranteed parameter, but not tested.

Note 9: Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW

AC Electrical Characteristics

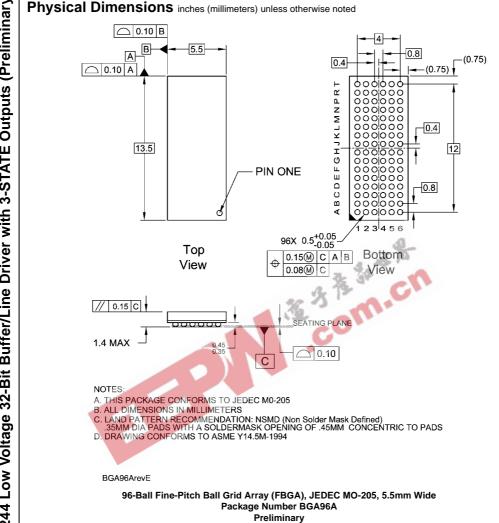
			Units			
Symbol	Parameter					
		$V_{CC}=3.3V\pm0.3V$		V _{CC} = 2.7V		Units
		Min	Max	Min	Max	
t _{PLH}	Propagation Delay Data to Output	1.2	3.5	1.2	3.9	ns
t_{PHL}		1.2	3.5	1.2	3.9	115
t _{PZH}	Output Enable Time	1.2	4.0	1.2	5.0	ns
t_{PZL}		1.2	5.0	1.2	6.5	115
t _{PHZ}	Output Disable Time	2.0	4.7	2.0	5.2	ns
t_{PLZ}		1.5	4.2	1.5	4.4	115

Capacitance (Note 10)

Symbol Parameter		Conditions	Typical	Units	
C _{IN}	Input Capacitance	$V_{CC} = 0V$, $V_I = 0V$ or V_{CC}	4	pF	
C _{OUT}	Output Capacitance	$V_{CC} = 3.0V$, $V_{O} = 0V$ or V_{CC}	8	pF	

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Note 10: Capacitance is measured at frequency f = 1 MHz, per MIL-STD-883, Method 3012.



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